

TABLE 10

IN THE CLAIMS:

Please rewrite Claims 1 and 20 as follows:

1. (Amended) A process for depositing a non-single crystalline SiGe-containing material onto a surface, comprising:
- providing a chemical vapor deposition chamber having disposed therein a substrate:
 - introducing a gas comprised of a higher-order silane and a germanium precursor to the chamber; and
 - depositing a non-single crystalline SiGe-containing film onto the substrate.
20. (Amended) A process for making a graded SiGe-containing film, comprising:
- providing a substrate disposed within a CVD chamber; and
 - depositing a graded SiGe-containing film onto the substrate by thermal CVD using a deposition gas comprising amounts of trisilane and a germanium precursor that are varied during deposition.

REMARKS

The specification has been amended as set forth above to rewrite the abstract and to replace the previously recited attorney docket nos. with the serial numbers of the corresponding patent applications. Claims 1 and 20 have been rewritten to correct minor typographical errors. These amendments do not narrow the scope of the claims and do not introduce new matter. The specification has been amended to correct the numbering of the Table 10 (previously referred to as a second Table 9), and to correct the corresponding references to Table 10 in paragraph [0107] in the as-filed application.

Specific changes to the specification and the amended claims are shown on a separate set of pages attached hereto and entitled VERSION WITH MARKINGS TO SHOW CHANGES MADE, which follows the signature page of this Amendment. On this set of pages, the insertions are underlined while **[deletions are bracketed and bolded]**.